2SA1961

Silicon PNP epitaxial planer type

For general amplification
Complementary to 2SC5419

Features

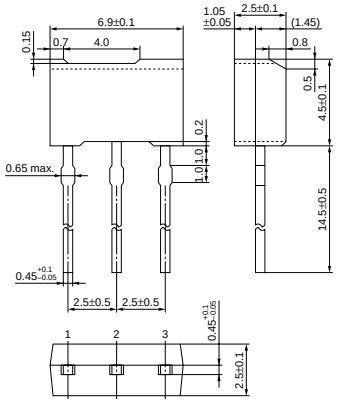
- High collector to emitter voltage V_{CEO}.

Absolute Maximum Ratings (Ta=25˚C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	–200	V
Collector to emitter voltage	V_{CEO}	–200	V
Emitter to base voltage	V_{EBO}	–5	V
Peak collector current	I_{CP}	– 0.1	A
Collector current	I_C	–70	mA
Collector power dissipation	P_C *	1	W
Junction temperature	T_j	150	˚C
Storage temperature	T_{stg}	–55 ~ +150	˚C

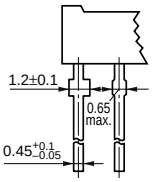
* Printed circuit board: Copper foil area of 1cm^2 or more, and the board thickness of 1.7mm for the collector portion

Unit: mm



Note: In addition to the lead type shown in the upper figure, the type as shown in the lower figure is also available.

1:Emitter
2:Collector
3:Base
MT2 Type Package



(HW type)

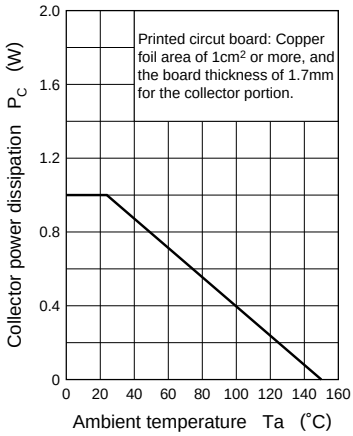
Electrical Characteristics (Ta=25˚C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector to emitter voltage	V_{CEO}	I_C = –100μA, I_B = 0	–200			V
Emitter to base voltage	V_{EBO}	I_E = –1μA, I_C = 0	–5			V
Forward current transfer ratio	h_{FE} *1	V_{CE} = –10V, I_C = –5mA	30		150	–
Collector to emitter saturation voltage	$V_{CE(sat)}$	I_C = –50mA, I_B = –5mA			–2.5	V
Transition frequency	f_T	V_{CB} = –5V, I_E = 10mA, f = 200MHz		30		MHz
Collector output capacitance	C_{ob}	V_{CB} = –10V, I_E = 0, f = 1MHz		7		pF

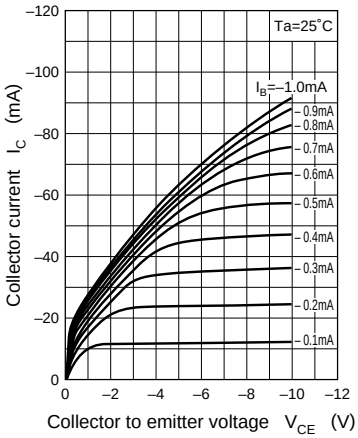
*1h_{FE} Rank classification

Rank	P	Q
h_{FE}	30 ~ 100	60 ~ 150

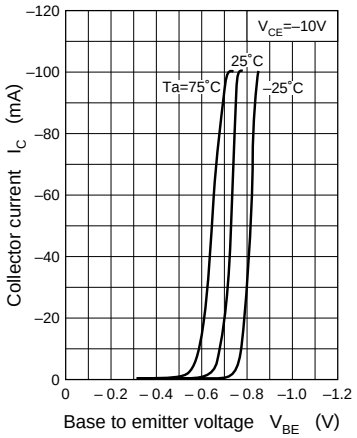
P_C — Ta



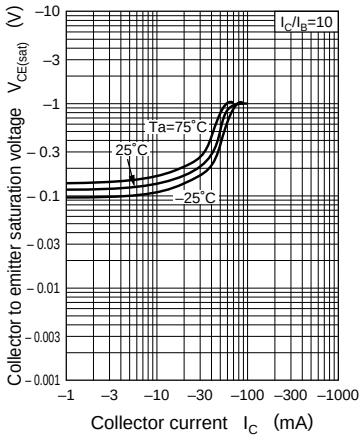
I_C — V_{CE}



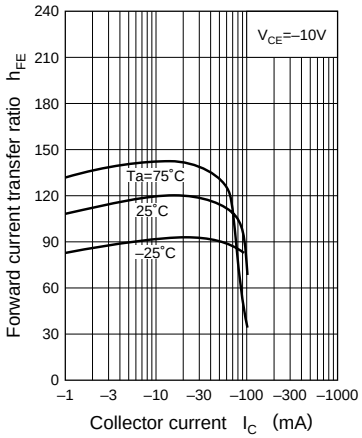
I_C — V_{BE}



$V_{CE(sat)}$ — I_C



h_{FE} — I_C



C_{ob} — V_{CB}